

ABSTRACT OF THE DISCLOSURE

A method of forming a ferroelectric film includes the steps of forming a layer by a material that takes a metal state in a reducing ambient and an  
5 oxide state in an oxidizing ambient, and depositing a ferroelectric film on a surface of the layer by supplying gaseous sources of the ferroelectric film and an oxidizing gas and causing a decomposition of the gaseous sources at the surface of said layer,  
10 wherein the step of depositing the ferroelectric film is started with a preparation step in which the state of the surface of said layer is controlled substantially to a critical point in which the layer changes from the metal state to the oxide state and  
15 from the oxide state to the metal state.